IRF740

Rev.H Jul.-2018



描述 / Descriptions

TO-220 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a TO-220 Plastic Package.

特征 / Features

低栅电荷,低反馈电容,开关速度快。

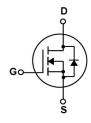
Low gate charge, low crss, fast switching.

用途 / Applications

用于高效 DC/DC 转换和功率开关。

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1: G PIN2: D PIN3: S

放大及印章代码 / hfe Classifications & Marking

见印章说明。 See Marking Instructions.

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极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit	
Drain-Source Voltage	V _{DSS}	400	V	
Drain Current	I _D (Tc=25℃)	10	А	
Drain Current	I _D (Tc=100℃)	6.3	Α	
Pulsed Drain Current	I _{DM}	40	Α	
Gate-Source Voltage	V_{GSS}	±30	V	
Avalanche Current	I _{AR}	10	Α	
Single Pulsed Avalanche Energy	E _{AS}	450	mJ	
Repetitive Avalanche Energy	E _{AR}	13.4	mJ	
Total Power Dissipation	P _D (Tc=25℃)	134	W	
Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 to 150	$^{\circ}$	

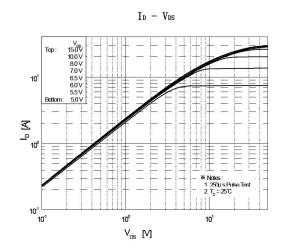
电性能参数 / Electrical Characteristics(Ta=25℃)

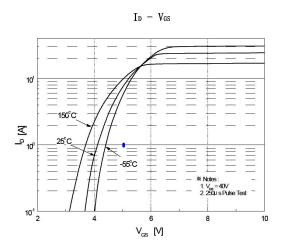
参数 Parameter	符号 Symbol	测试条件 Test Conditions		最小值 Min	典型值 Typ	最大值 Max	单位 Unit	
Zero Gate Voltage Drain Current	BV _{DSS}	V _{GS} =0V I _D =250µA		400	тур	IVIGA	V	
Zana Osta Walleria Busin Osmanla	I _{DSS}	V _{DS} =400V	V _{GS} =0V			10	μA	
Zero Gate Voltage Drain Current		V _{DS} =320V	T _C =125℃			100	μA	
Gate-Body Leakage Current Forward	I _{GSS}	V _{GS} =±30V	V _{DS} =0V			±0.1	μA	
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}	I _D =250μΑ	2.0		4.0	V	
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V	I _D =5.0A		0.44	0.55	Ω	
Forward Transconductance	g FS	V _{DS} =40V	I _D =5.0A		9.0		S	
Forward On Voltage	V_{SD}	V _{GS} =0V I _S =10A				1.5	V	
Input Capacitance	C _{iss}				1570	2040		
Output Capacitance	C _{oss}	V _{DS} =25V f=1.0MHz	V _{GS} =0V		150	195	pF	
Reverse Transfer Capacitance	C _{rss}	1-1.0WH12			15	20		
Turn-On Delay Time	t _{d(on)}				25	60		
Turn-On Rise Time	t _r	V_{DD} =200 V I_{D} =10 A R_{G} =25 Ω			75	160	ns	
Turn-Off Delay Time	t _{d(off)}				115	240		
Turn-Off Fall Time	t _f				70	150		

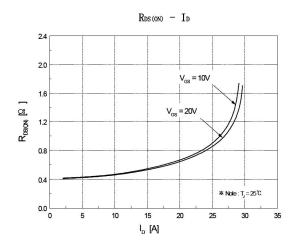
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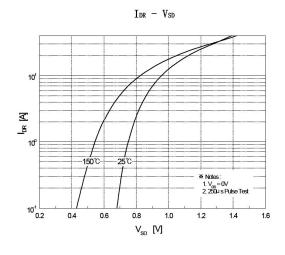
蓝箭电子BLUE ROCKET ELECTRONICS DATA SHEET

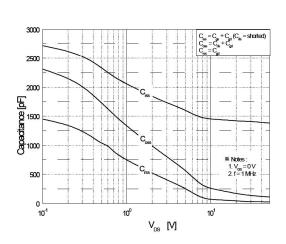
电参数曲线图 / Electrical Characteristic Curve

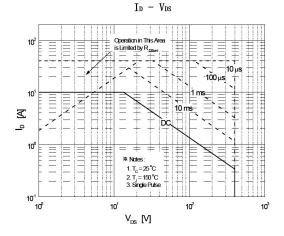










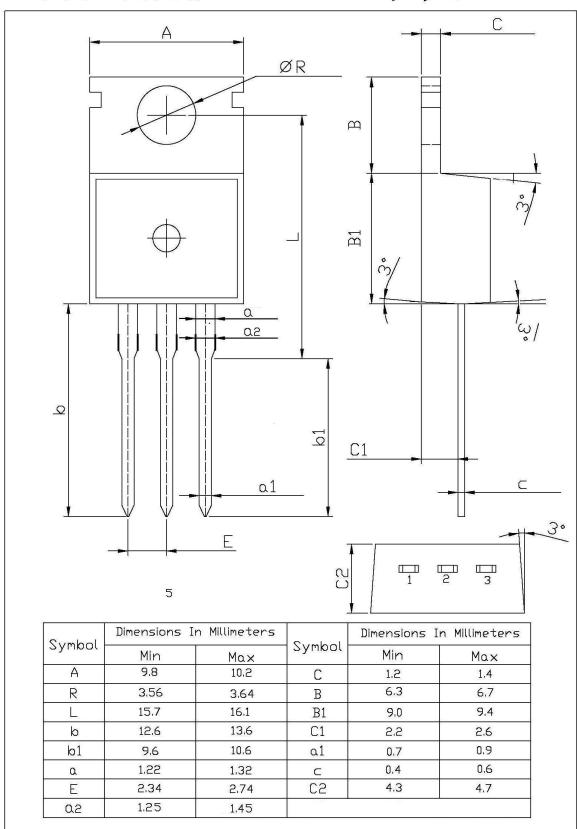


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外形尺寸图 / Package Dimensions



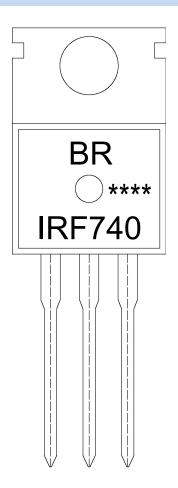


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印章说明 / Marking Instructions



说明:

 BR:
 为公司代码

 IRF740:
 为产品型号

****: 为生产批号代码,随生产批号变化。

Note:

BR: Company Code

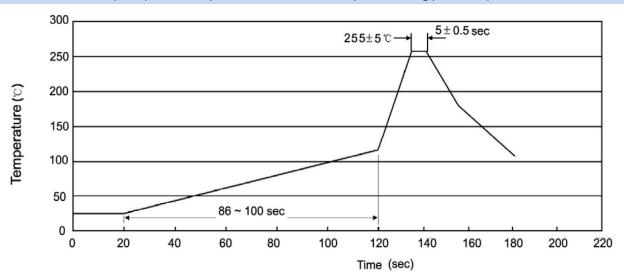
IRF740: Product Type.

****: Lot No. Code, code change with Lot No.

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波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明:

- 1、预热温度 25~150℃, 时间 60~90sec;
- 2、峰值温度 255±5℃, 时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10℃/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
- 3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度: 270±5℃ 时间: 10±1 sec. Temp.:270±5℃ Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type	Units 包装数量					Dimension 包装尺寸 (unit: mm³)		
封装形式	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type	Units 包装数量					Dimension 包装尺寸 (unit: mm³)		
封装形式	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1.000	5	5.000	532×31.4×5.5	555×164×50	575×290×180

使用说明 / Notices

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